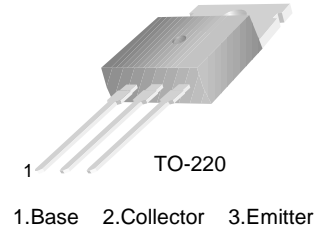


■■ APPLICATION: High - Voltage, High - Speed Power Switching Applications.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER		SYMBOL	RATING	UNIT
Collector-base voltage		VCBO	700	V
Collector-emitter voltage		VCEO	400	V
Emitter-base voltage		VEBO	9	V
Collector current		IC	8	A
Base current		IB	4	A
Collector Power Dissipation	(Tc=25°C)	Pd	80	W
	(Ta=25°C)		2	
Junction Temperature		Tj	150	°C
Storage Temperature Range		Tstg	-55-150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	TEST CONDITION	RATING			UNIT
			MIN.	TYP.	MAX.	
DC Current Gain	h _{FE}	Vce=5 V, Ic=2A	8		60	β
Collector-Base Breakdown Voltage	BVcbo	Ic=1 mA ,Ie=0	700			V
Collector-Emitter Breakdown Voltage	BVceo	Ic=10 mA ,Ib=0	400			V
Emitter-Base Breakdown Voltage	BVebo	Ie=1 mA ,Ic=0	9			V
Collector Cut-off Current	Icbo	Vcb=700 V ,Ie=0			1	mA
Emitter Cut-off Current	Iebo	Veb=9 V ,Ic=0			1	mA
Collector-Emitter Saturation Voltage	Vce(sat)	Ic=5A ,Ib=1A			2	V
Base-Emitter Saturation Voltage	Vbe(sat)	Ic=5A ,Ib=1A			1.6	V
Gain bandwidth product	f _T	Vce=10V, Ic=500mA, f=1.0MHz	4			MHz
Turn on Time	ton	Vce=10V, Ic=2A, IB1=IB2=400mA			1.6	uS
Storage Time	ts				3.5	uS
Fall Time	tf				0.7	uS

■■ h_{FE} Classification And Marking

Mark	D13007				
Classification	A	B	C	D	E
h _{FE}	8-25	20-35	30-45	40-55	50-60